DF451

FAST RECOVERY DIODE

APPLICATIONS

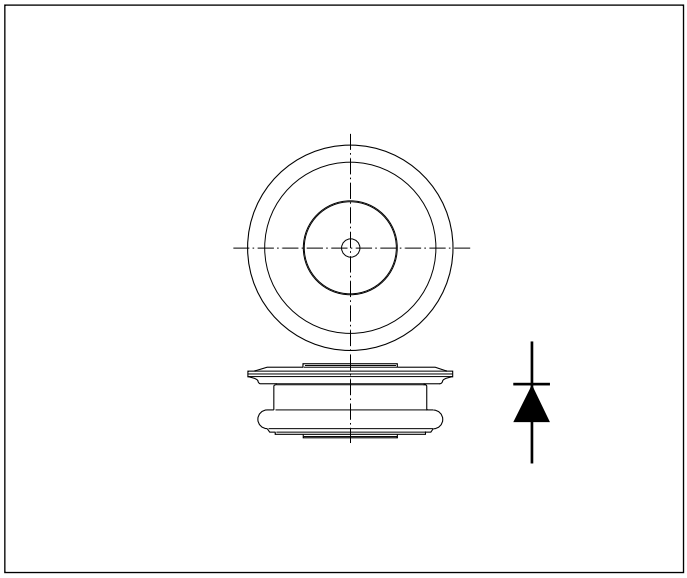
- Induction Heating.
- A.C. Motor Drives.
- Inverters And Choppers.
- Welding.
- High Frequency Rectification.
- UPS.

KEY PARAMETERS

V_{RRM}	1600V
$I_{F(AV)}$	295A
I_{FSM}	3500A
Q_r	25μC
t_{rr}	1.22μs

FEATURES

- Double Side Cooling.
- High Surge Capability.
- Low Recovery Charge.



Outline type code: M771. See package outlines for further information.

VOLTAGE RATINGS

Type Number	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DF451 16	1600	$V_{RSM} = V_{RRM} + 100V$
DF451 14	1400	
DF451 12	1200	
DF451 10	1000	
DF451 08	800	
DF451 06	600	

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
Double Side Cooled				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	295	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	543	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	391	A
Single Side Cooled (Anode side)				
$I_{F(AV)}$	Mean forward current	Half wave resistive load, T_{case} = 65°C	220	A
$I_{F(RMS)}$	RMS value	T_{case} = 65°C	348	A
I_F	Continuous (direct) forward current	T_{case} = 65°C	285	A

SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 0% $V_{RRM,}$ T_j = 150°C	3.5	kA
I^2t	I^2t for fusing		61.25×10^3	A^2s
I_{FSM}	Surge (non-repetitive) forward current	10ms half sine; with 50% $V_{RRM,}$ T_j = 150°C	2.8	kA
I^2t	I^2t for fusing		39.2×10^3	A^2s

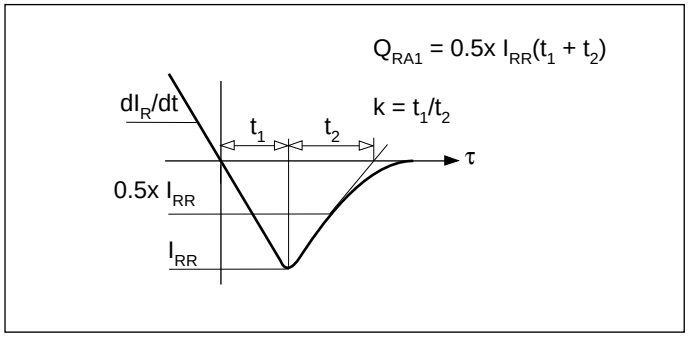
THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions		Min.	Max.	Units
$R_{th(j-c)}$	Thermal resistance - junction to case	Double side cooled	dc	-	0.07	°C/W
		Single side cooled	Anode dc	-	0.133	°C/W
			Cathode dc	-	0.147	°C/W
$R_{th(c-h)}$	Thermal resistance - case to heatsink	Clamping force 5.0kN with mounting compound	Double side	-	0.02	°C/W
			Single side	-	0.02	°C/W
T_{vj}	Virtual junction temperature	On-state (conducting)		-	150	°C
T_{stg}	Storage temperature range			-55	150	°C
-	Clamping force			4.5	5.5	kN

CHARACTERISTICS

Symbol	Parameter	Conditions	Typ.	Max.	Units
V_{FM}	Forward voltage	At 600A peak, T_{case} = 25°C	-	2.65	V
I_{RRM}	Peak reverse current	At V_{RRM}, T_{case} = 125°C	-	100	mA
t_{rr}	Reverse recovery time	I_F = 500A, di_{RR}/dt = -80A/µs T_{case} = 125°C, V_R = 100V	1.22	-	µs
Q_{RA1}	Recovered charge (50% chord)		-	25	µC
I_{RM}	Reverse recovery current		-	40	A
K	Soft factor		1.7	-	-
V_{TO}	Threshold voltage	At T_{vj} = 125°C	-	1.6	V
r_T	Slope resistance	At T_{vj} = 125°C	-	1.5	mΩ
V_{FRM}	Forward recovery voltage	di/dt = 1000A/µs, T_j = 125°C	-	40	V

DEFINITION OF K FACTOR AND Q_{RA1}



CURVES

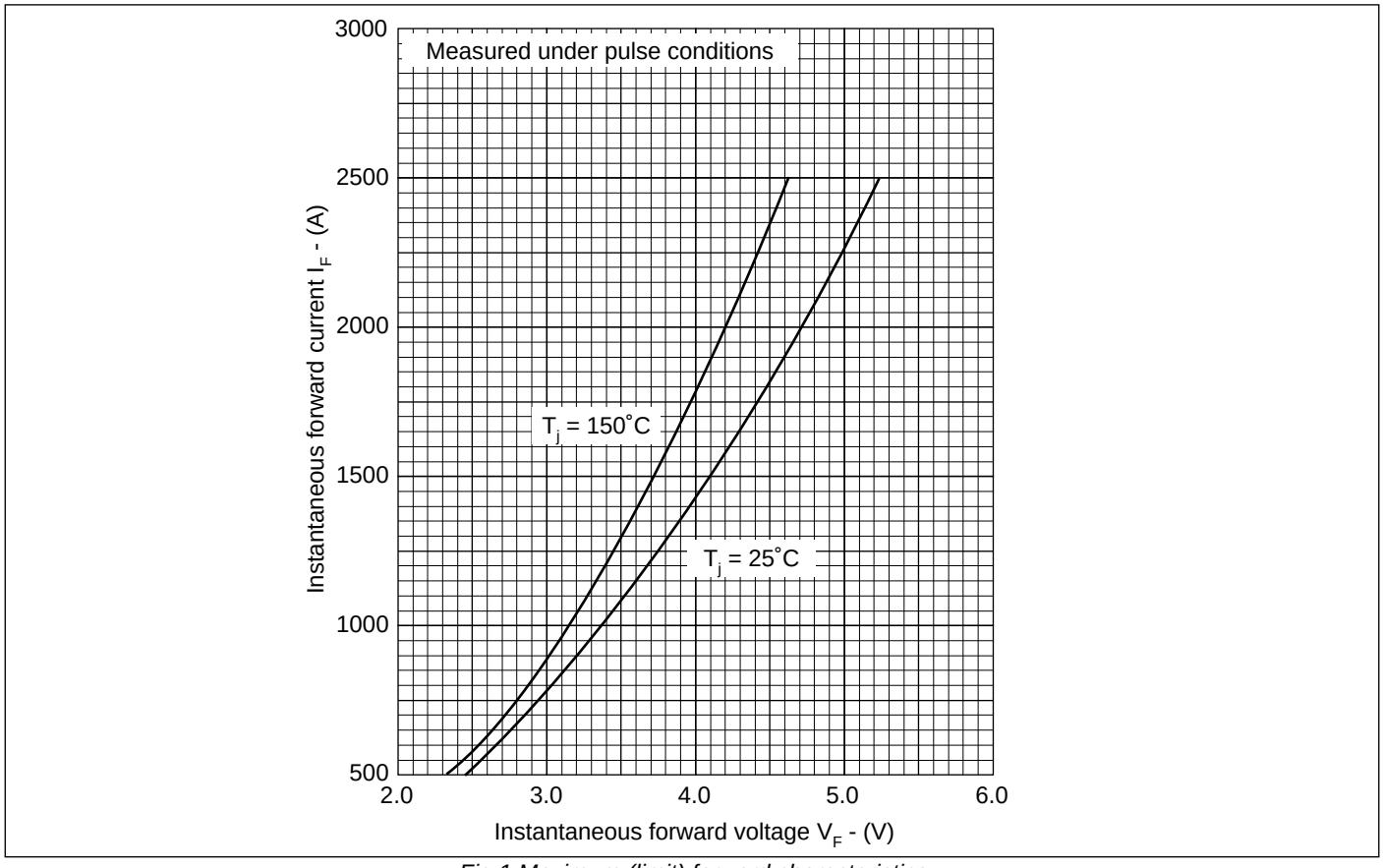


Fig.1 Maximum (limit) forward characteristics

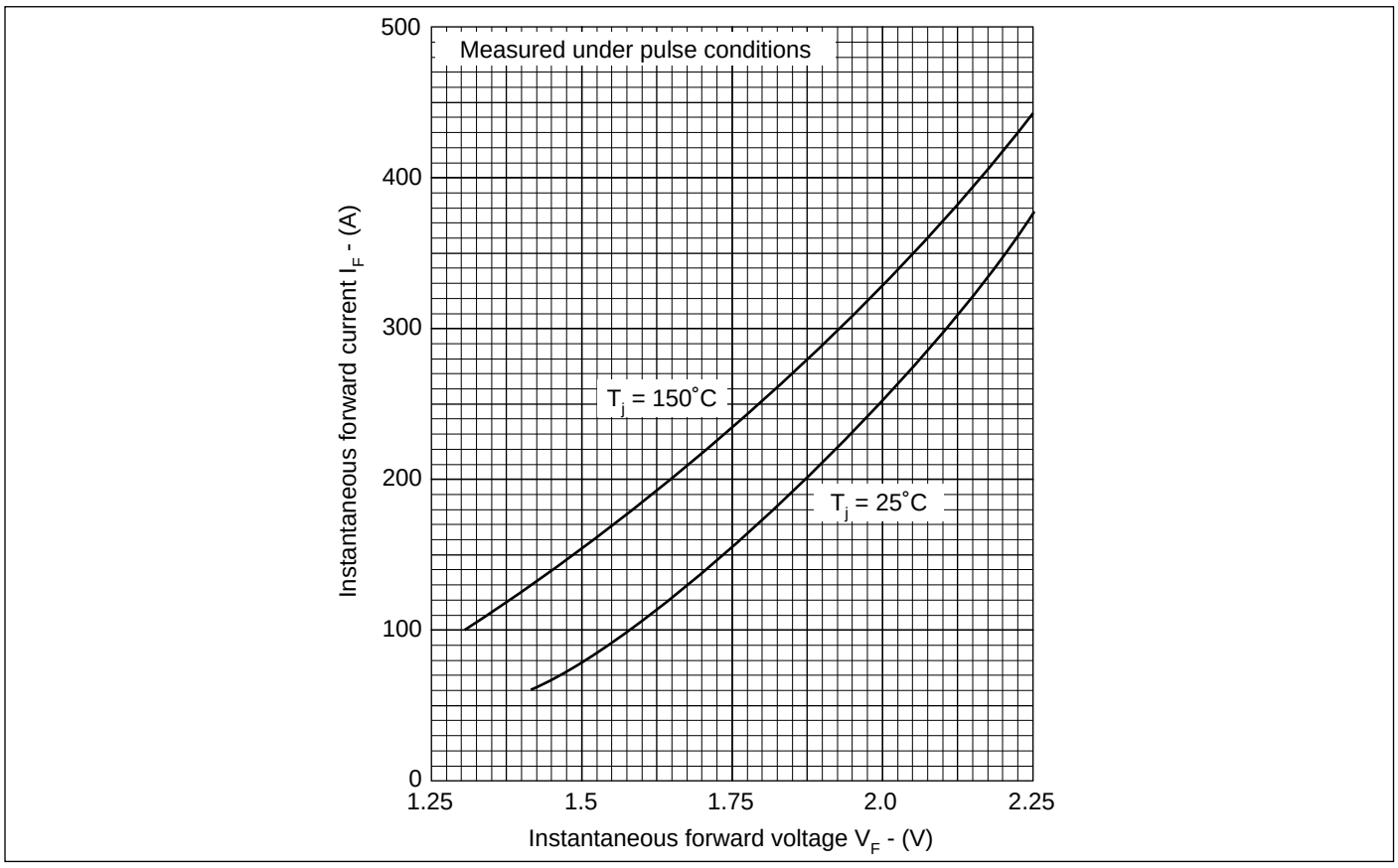


Fig.2 Maximum (limit) forward characteristics

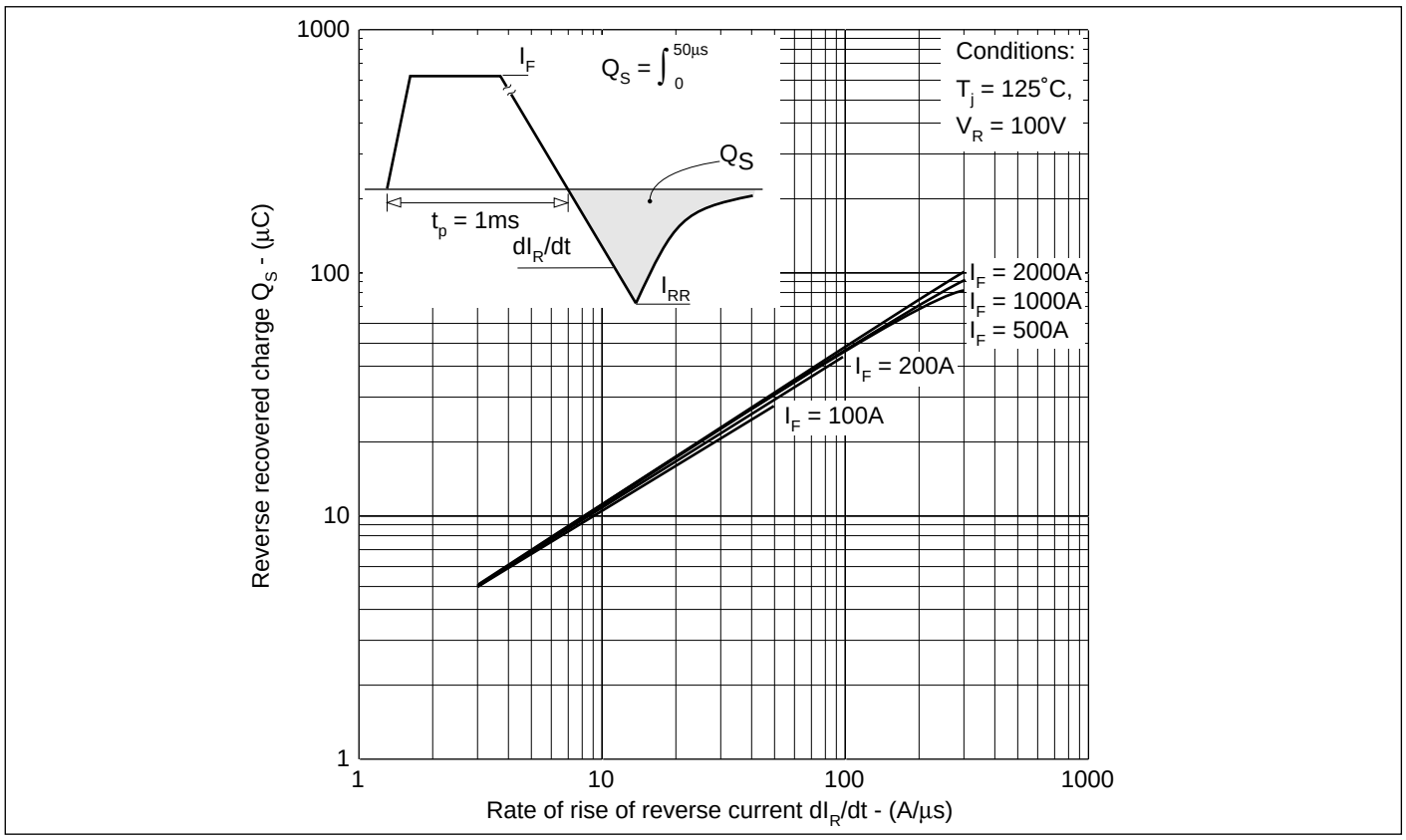


Fig.3 Recovered charge

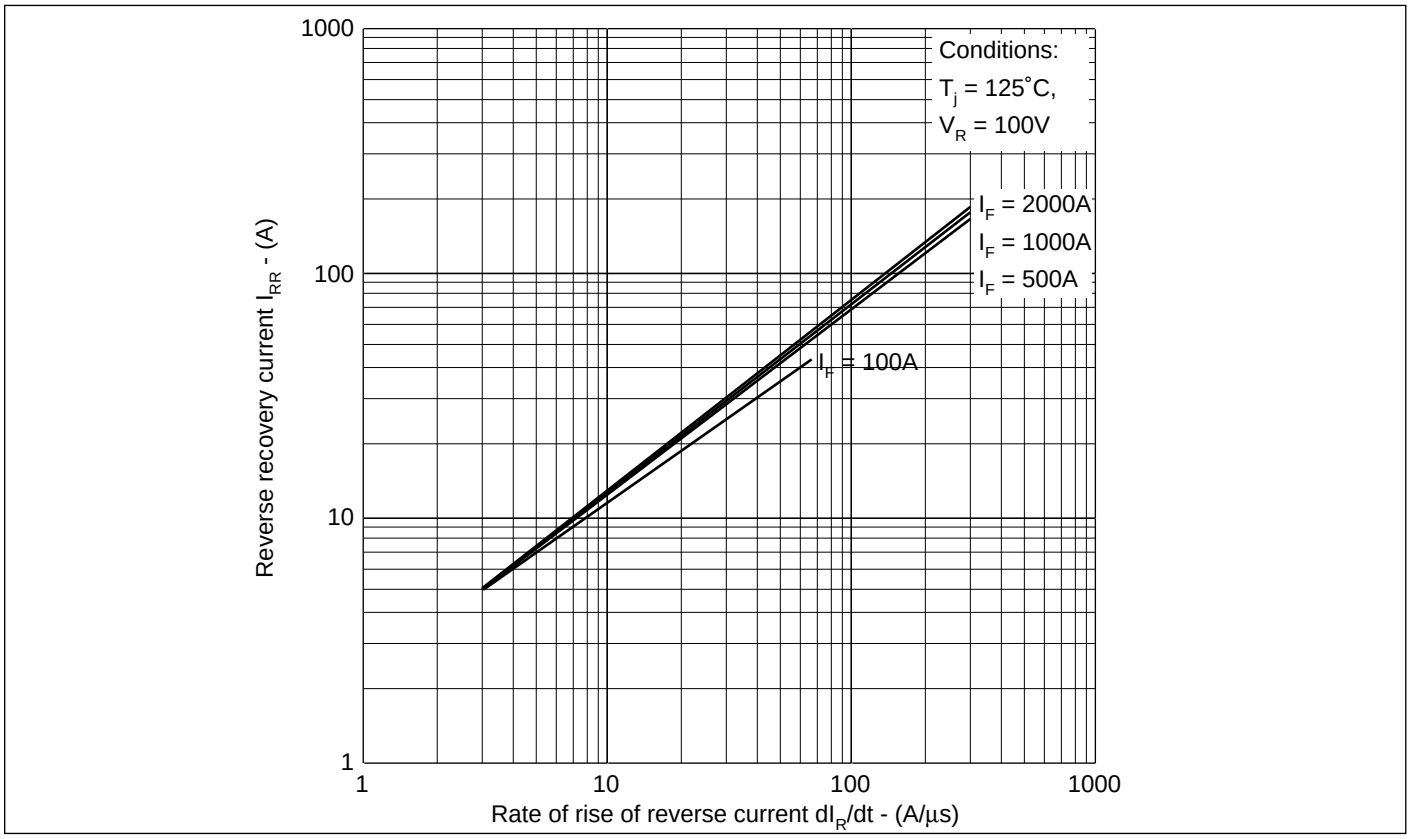


Fig.4 Typical reverse recovery current vs rate of rise of forward current

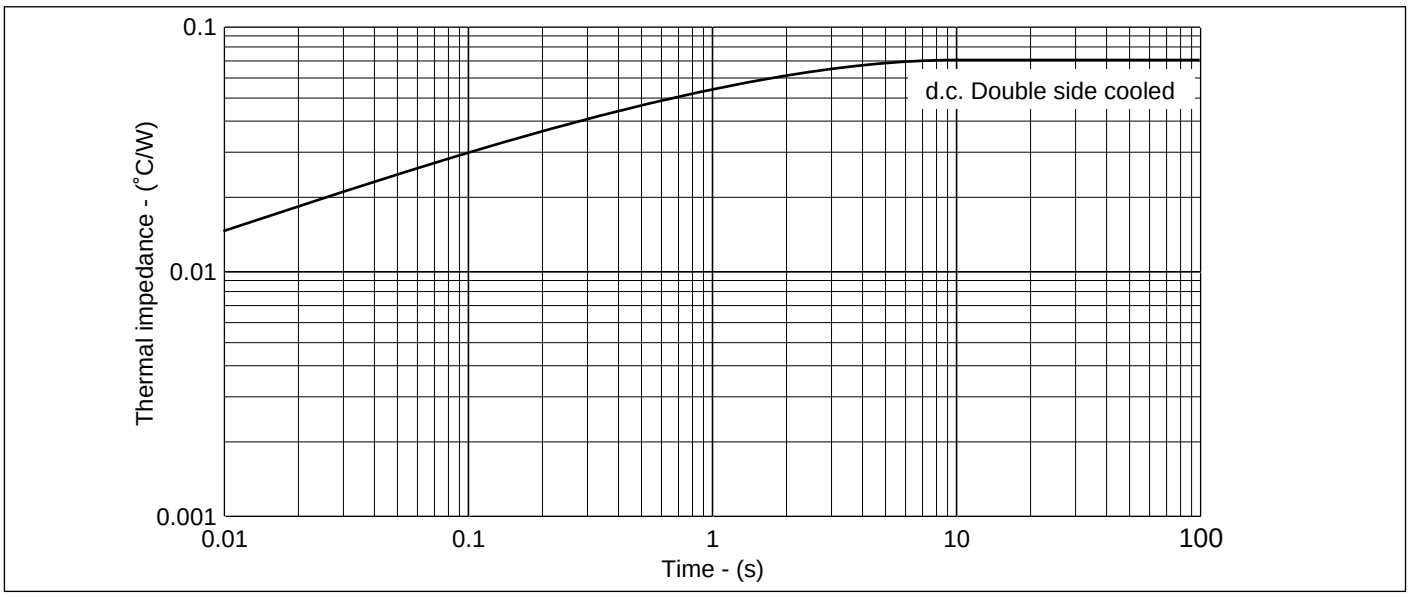
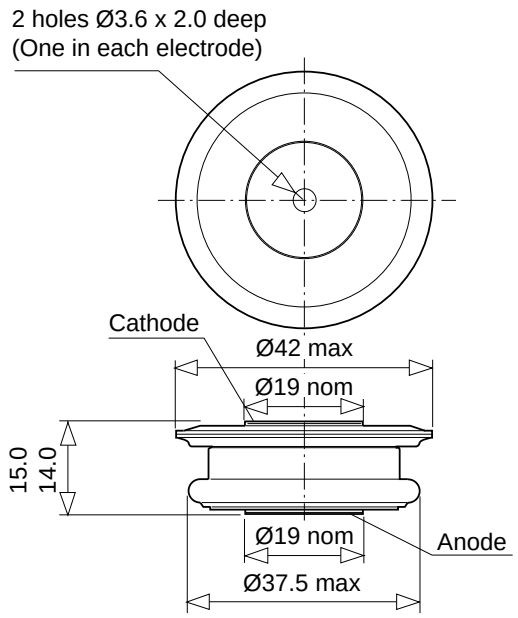


Fig.5 Maximum (limit) transient thermal impedance - junction to case - (˚C/W)

PACKAGE DETAILS - M771

For further package information, please contact your local Customer Service Centre. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



Weight: 50g

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